

Abstract

The invention relates to a method for the production of masks, in particular for the production of alternating phase shift masks (1), or of chromeless phase shift masks or phase shift masks structured by quartz etching, respectively, as well as to a mask (1), in particular photomask, for the production of semiconductor devices, comprising at least one product field area (6a) and a compensation structure (5) positioned outside the product field area (6a), wherein the compensation structure (5) comprises at least one electroconductive region (8b) that is electrically connected with the product field area (6a).